
HM514400C Series

1,048,576-word × 4-bit Dynamic Random Access Memory

HITACHI

Description

The Hitachi HM514400C is a CMOS dynamic RAM organized 1,048,576-word × 4-bit. HM514400C has realized higher density, higher performance and various functions by employing 0.8 μm CMOS process technology and some new CMOS circuit design technologies. The HM514400C offers Fast Page Mode as a high speed access mode. Multiplexed address input permits the HM514400C to be packaged in standard 300-mil 26-pin plastic SOJ, standard 400-mil 20-pin plastic ZIP and 26-pin plastic TSOP II.

Features

- Single 5 V (±10%)
- High speed
 - Access time: 60 ns/70 ns/80 ns (max)
- Low power dissipation
 - Active mode: 605 mW/550 mW/495 mW (max)
 - Standby mode: 11 mW (max)
0.55 mW (max) (L-version)
- Fast page mode capability
- 1024 refresh cycles : 16 ms
: 128 ms (L-version)
- 3 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh
 - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh
 - Hidden refresh
- Test function
- Battery backup operation (L-version)

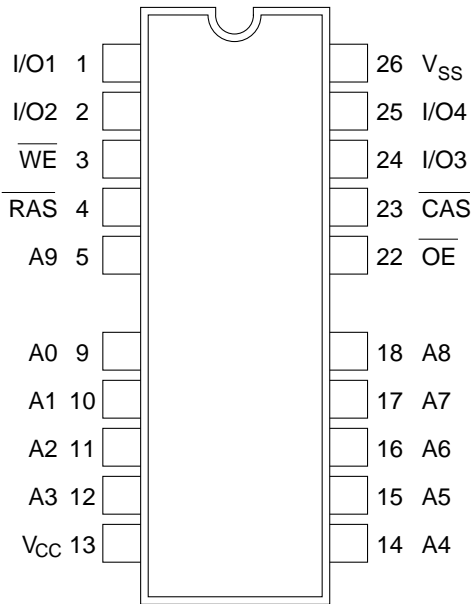
HM514400C Series

Ordering Information

Type No.	Access Time	Package
HM514400CS-6	60 ns	300-mil 26-pin plastic SOJ (CP-26/20D)
HM514400CS-7	70 ns	
HM514400CS-8	80 ns	
HM514400CLS-6	60 ns	
HM514400CLS-7	70 ns	
HM514400CLS-8	80 ns	
HM514400CZ-6	60 ns	400-mil 20-pin plastic ZIP (ZP-20)
HM514400CZ-7	70 ns	
HM514400CZ-8	80 ns	
HM514400CLZ-6	60 ns	
HM514400CLZ-7	70 ns	
HM514400CLZ-8	80 ns	
HM514400CTT-6	60 ns	26-pin plastic TSOPII (TTP-26/20D)
HM514400CTT-7	70 ns	
HM514400CTT-8	80 ns	
HM514400CLTT-6	60 ns	
HM514400CLTT-7	70 ns	
HM514400CLTT-8	80 ns	

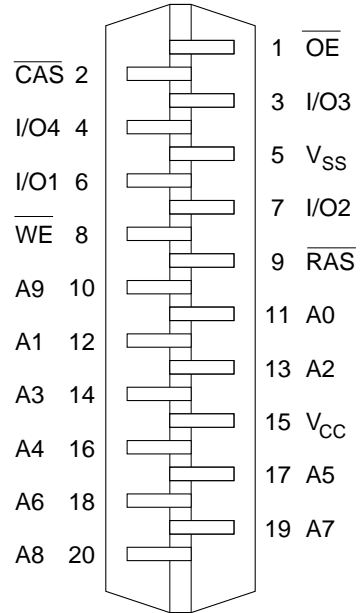
Pin Arrangement

HM514400CS/CLS Series



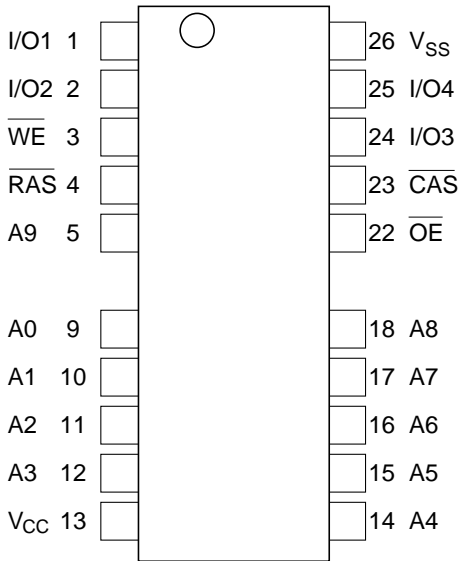
(Top view)

HM514400CZ/CLZ Series



(Bottom view)

HM514400CTT/CLTT Series

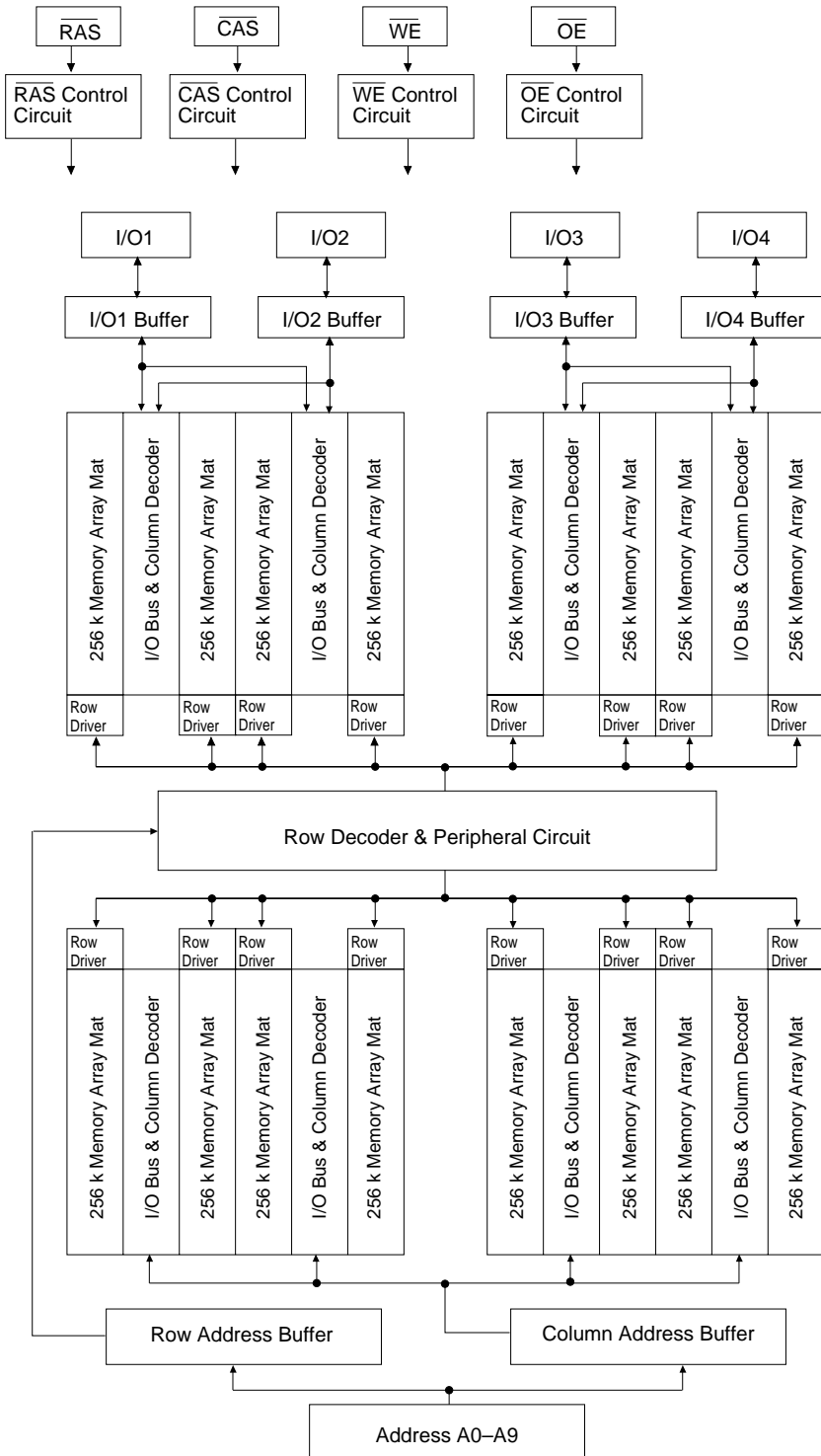


(Top view)

Pin Description

Pin Name	Function
A0 to A9	Address input
A0 to A9	Refresh address input
I/O1 to I/O4	Data-in/Data-out
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{WE}}$	Read/Write enable
$\overline{\text{OE}}$	Output enable
V _{CC}	Power (+5 V)
V _{SS}	Ground

Block Diagram



HM514400C Series

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	-1.0 to +7.0	V
Supply voltage relative to V_{SS}	V_{CC}	-1.0 to +7.0	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	1.0	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C

Recommended DC Operating Conditions ($T_a = 0$ to $+70^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V_{SS}	0	0	0	V	
	V_{CC}	4.5	5.0	5.5	V	1
Input high voltage	V_{IH}	2.4	—	6.5	V	1
Input low voltage	V_{IL}	-1.0	—	0.8	V	1

Note: 1. All voltage referred to V_{SS} .

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 5 V ± 10%, V_{SS} = 0 V)

Parameter	Symbol	HM514400C						Unit	Test Conditions
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Operating current ^{*1, *2}	I _{CC1}	—	110	—	100	—	90	mA	$\overline{\text{RAS}}, \overline{\text{CAS}}$ cycling t _{RC} = min
Standby current	I _{CC2}	—	2	—	2	—	2	mA	TTL interface $\overline{\text{RAS}}, \overline{\text{CAS}} = V_{\text{IH}}$ Dout = High-Z
		—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} \geq V_{\text{CC}} - 0.2 \text{ V}$ Dout = High-Z
Standby current (L-version) ^{*4}	I _{CC2}	—	100	—	100	—	100	μA	CMOS interface $\overline{\text{RAS}}, \overline{\text{CAS}} = V_{\text{IH}}$ $\overline{\text{WE}}, \overline{\text{OE}}, \text{Address}$ and Din = V _{IH} or V _{IL} Dout = High-Z
$\overline{\text{RAS}}$ -only refresh current ^{*2}	I _{CC3}	—	110	—	100	—	90	mA	t _{RC} = min
Standby current ^{*1}	I _{CC5}	—	5	—	5	—	5	mA	$\overline{\text{RAS}} = V_{\text{IH}}$, $\overline{\text{CAS}} = V_{\text{IL}}$ Dout = enable
$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh current	I _{CC6}	—	110	—	100	—	90	mA	t _{RC} = min
Fast page mode current ^{*1, *3}	I _{CC7}	—	110	—	100	—	90	mA	t _{PC} = min
Battery backup current ^{*4} (Standby with CBR refresh) (L-version)	I _{CC10}	—	200	—	200	—	200	μA	t _{RC} = 125 μs t _{RAS} ≤ 1 μs $\overline{\text{WE}} = V_{\text{IH}}$, $\overline{\text{CAS}} = V_{\text{IL}}$ $\overline{\text{OE}}, \text{Address}$ and Din = V _{IH} or V _{IL} Dout = High-Z
Input leakage current	I _{LI}	-10	10	-10	10	-10	10	μA	0 V ≤ Vin ≤ 7 V
Output leakage current	I _{LO}	-10	10	-10	10	-10	10	μA	0 V ≤ Vout ≤ 7 V Dout = disable
Output high voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = -5 mA
Output low voltage	V _{OL}	0	0.4	0	0.4	0	0.4	V	Low Iout = 4.2 mA

Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed twice or less while $\overline{\text{RAS}} = V_{\text{IL}}$.

3. Address can be changed once or less while $\overline{\text{CAS}} = V_{\text{IH}}$.

4. V_{CC} - 0.2 V ≤ V_{IH} ≤ 6.5 V and 0 V ≤ V_{IL} ≤ 0.2 V.

HM514400C Series

Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{I1}	—	5	pF	1
Input capacitance (Clocks)	C_{I2}	—	7	pF	1
Output capacitance (Data-in, Data-out)	$C_{I/O}$	—	7	pF	1, 2

Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
2. $\overline{\text{CAS}} = V_{IH}$ to disable Dout.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)^{*1, *14, *15, *16}

Test Conditions

- Input rise and fall time : 5 ns
- Input timing reference levels : 0.8 V, 2.4 V
- Output load : 2 TTL gate + C_L (100 pF) (Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Random read or write cycle time	t_{RC}	110	—	130	—	150	—	ns	
\overline{RAS} precharge time	t_{RP}	40	—	50	—	60	—	ns	
\overline{RAS} pulse width	t_{RAS}	60	10000	70	10000	80	10000	ns	19
\overline{CAS} pulse width	t_{CAS}	15	10000	20	10000	20	10000	ns	20
Row address setup time	t_{ASR}	0	—	0	—	0	—	ns	
Row address hold time	t_{RAH}	10	—	10	—	10	—	ns	
Column address setup time	t_{ASC}	0	—	0	—	0	—	ns	
Column address hold time	t_{CAH}	15	—	15	—	15	—	ns	
\overline{RAS} to \overline{CAS} delay time	t_{RCD}	20	45	20	50	20	60	ns	8
\overline{RAS} to column address delay time	t_{RAD}	15	30	15	35	15	40	ns	9
\overline{RAS} hold time	t_{RSH}	15	—	20	—	20	—	ns	
\overline{CAS} hold time	t_{CSH}	60	—	70	—	80	—	ns	
\overline{CAS} to \overline{RAS} precharge time	t_{CRP}	10	—	10	—	10	—	ns	
\overline{OE} to Din delay time	t_{ODD}	15	—	20	—	20	—	ns	
\overline{OE} delay time from Din	t_{DZO}	0	—	0	—	0	—	ns	
\overline{CAS} setup time from Din	t_{DZC}	0	—	0	—	0	—	ns	
Transition time (rise and fall)	t_T	3	50	3	50	3	50	ns	7
Refresh period	t_{REF}	—	16	—	16	—	16	ms	
Refresh period (L-version)	t_{REF}	—	128	—	128	—	128	ms	

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Read Cycle

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	60	—	70	—	80	ns	2, 3, 17
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	15	—	20	—	20	ns	3, 4, 13, 17
Access time from address	t_{AA}	—	30	—	35	—	40	ns	3, 5, 13, 17
Access time from $\overline{\text{OE}}$	t_{OAC}	—	15	—	20	—	20	ns	3, 17
Read command setup time	t_{RCS}	0	—	0	—	0	—	ns	
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	—	0	—	0	—	ns	18
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	0	—	ns	18
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	30	—	35	—	40	—	ns	
Output buffer turn-off time	t_{OFF1}	0	15	0	20	0	20	ns	6
Output buffer turn-off time to $\overline{\text{OE}}$	t_{OFF2}	0	15	0	20	0	20	ns	6
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	15	—	20	—	20	—	ns	
$\overline{\text{OE}}$ pulse width	t_{OEP}	15	—	20	—	20	—	ns	

Write Cycle

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Write command setup time	t_{WCS}	0	—	0	—	0	—	ns	10
Write command hold time	t_{WCH}	15	—	15	—	15	—	ns	
Write command pulse width	t_{WP}	10	—	10	—	10	—	ns	
Write command to $\overline{\text{RAS}}$ lead time	t_{RWL}	15	—	20	—	20	—	ns	
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	15	—	20	—	20	—	ns	
Data-in setup time	t_{DS}	0	—	0	—	0	—	ns	11
Data-in hold time	t_{DH}	15	—	15	—	15	—	ns	11

Read-Modify-Write Cycle

		HM514400C							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Read-modify-write cycle time	t_{RWC}	150	—	180	—	200	—	ns	
\overline{RAS} to \overline{WE} delay time	t_{RWD}	80	—	95	—	105	—	ns	10
\overline{CAS} to \overline{WE} delay time	t_{CWD}	35	—	45	—	45	—	ns	10
Column address to \overline{WE} delay time	t_{AWD}	50	—	60	—	65	—	ns	10
\overline{OE} hold time from \overline{WE}	t_{OEh}	15	—	20	—	20	—	ns	

Refresh Cycle

		HM514400C							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
\overline{CAS} setup time (CBR refresh cycle)	t_{CSR}	10	—	10	—	10	—	ns	
\overline{CAS} hold time (CBR refresh cycle)	t_{CHR}	10	—	10	—	10	—	ns	
\overline{RAS} precharge to \overline{CAS} hold time	t_{RPC}	10	—	10	—	10	—	ns	
\overline{CAS} precharge time in normal mode	t_{CPN}	10	—	10	—	10	—	ns	

Fast Page Mode Cycle

		HM514400C							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Fast page mode cycle time	t_{PC}	40	—	45	—	50	—	ns	
Fast page mode \overline{CAS} precharge time	t_{CP}	10	—	10	—	10	—	ns	
Fast page mode \overline{RAS} pulse width	t_{RASC}	—	100000	—	100000	—	100000	ns	12
Access time from \overline{CAS} precharge	t_{ACP}	—	35	—	40	—	45	ns	3, 13, 17
\overline{RAS} hold time from \overline{CAS} precharge	t_{RHCP}	35	—	40	—	45	—	ns	

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Fast Page Mode Read-Modify-Write Cycle

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Fast page mode read-modify-write cycle time	t_{PCM}	80	—	95	—	100	—	ns	
Fast page mode read-modify-write cycle \overline{CAS} precharge to \overline{WE} delay time	t_{CPW}	55	—	65	—	70	—	ns	10

Test Mode Cycle

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
Test mode \overline{WE} setup time	t_{WS}	0	—	0	—	0	—	ns	
Test mode \overline{WE} hold time	t_{WH}	10	—	10	—	10	—	ns	

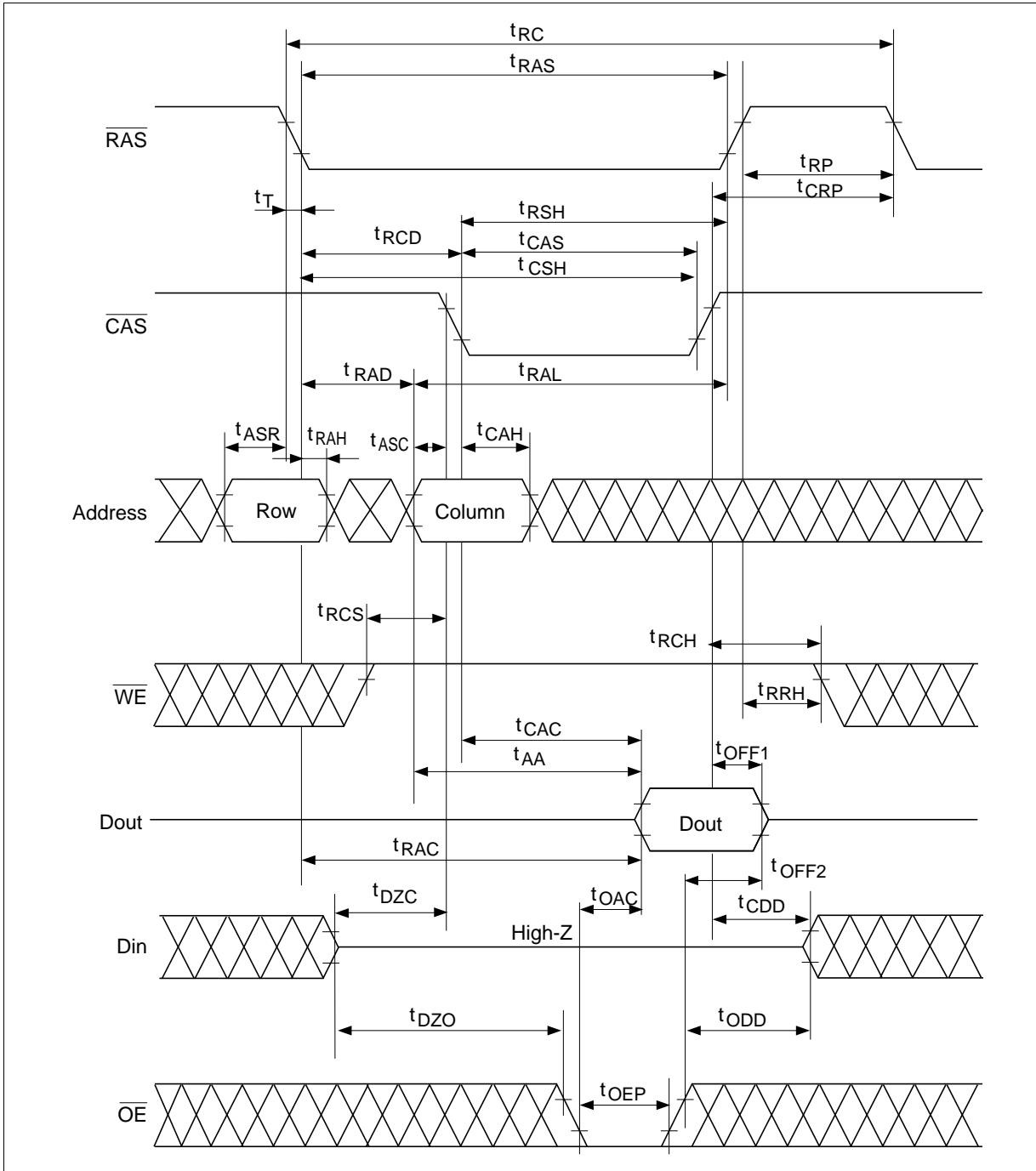
Counter Test Cycle

Parameter	Symbol	HM514400C						Unit	Notes
		-6		-7		-8			
		Min	Max	Min	Max	Min	Max		
\overline{CAS} precharge time in counter test cycle	t_{CPT}	40	—	40	—	40	—	ns	

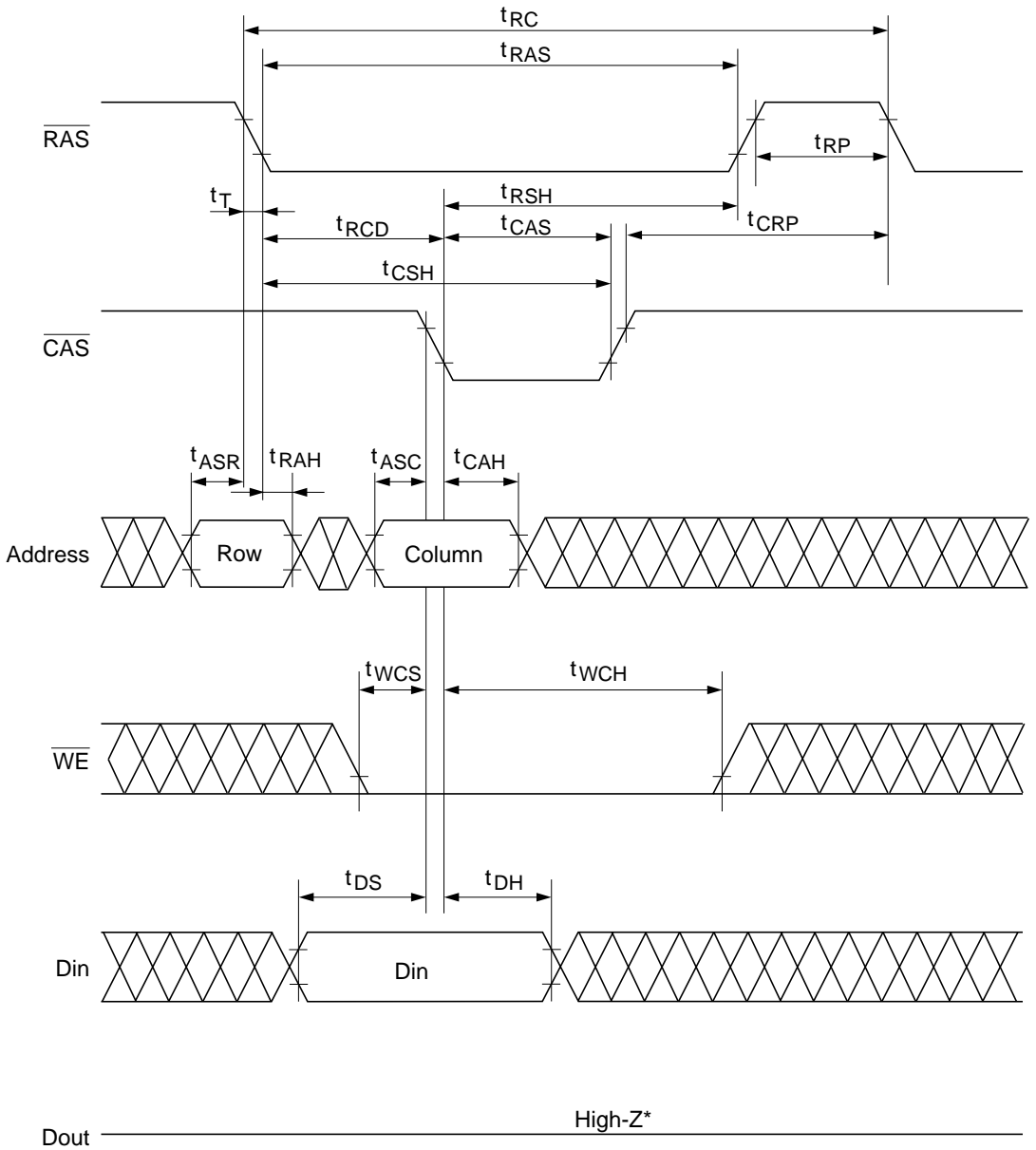
- Notes:
1. AC measurements assume $t_T = 5$ ns.
 2. Assumes that $t_{RCD} \leq t_{RCD}(\text{max})$ and $t_{RAD} \leq t_{RAD}(\text{max})$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
 3. Measured with a load circuit equivalent to 2 TTL loads and 100 pF.
 4. Assumes that $t_{RCD} \geq t_{RCD}(\text{max})$ and $t_{RAD} \leq t_{RAD}(\text{max})$.
 5. Assumes that $t_{RCD} \leq t_{RCD}(\text{max})$ and $t_{RAD} \geq t_{RAD}(\text{max})$.
 6. $t_{OFF}(\text{max})$ defines the time at which the output achieves the open circuit condition and is not referred to output voltage levels.
 7. $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL} .
 8. Operation with the $t_{RCD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met, $t_{RCD}(\text{max})$ is specified as a reference point only, if t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
 9. Operation with the $t_{RAD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met, $t_{RAD}(\text{max})$ is specified as a reference point only, if t_{RAD} is greater than the specified $t_{RAD}(\text{max})$ limit, then access time is controlled exclusively by t_{AA} .
 10. t_{WCS} , t_{RWD} , t_{CWD} , t_{CPW} and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{WCS} \geq t_{WCS}(\text{min})$, the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{RWD} \geq t_{RWD}(\text{min})$, $t_{CWD} \geq t_{CWD}(\text{min})$, $t_{CPW} \geq t_{CPW}(\text{min})$ and $t_{AWD} \geq t_{AWD}(\text{min})$, the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
 11. These parameters are referred to $\overline{\text{CAS}}$ leading edge in an early write cycle and to $\overline{\text{WE}}$ leading edge in a delayed write or read-modify-write cycle.
 12. t_{RASC} defines $\overline{\text{RAS}}$ pulse width in fast page mode cycles.
 13. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{ACP} .
 14. An initial pause of 100 μs is required after power up followed by a minimum of eight initialization cycles ($\overline{\text{RAS}}$ -only refresh cycle or $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle). If the internal refresh counter is used, a minimum of eight $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycles is required.
 15. In delayed write or read-modify-write cycles, $\overline{\text{OE}}$ must disable output buffer prior to applying data to the device.
 16. Test mode operation specified in this data sheet is 2-bit test function controlled by control address bits - - - CA0. This test mode operation can be performed by $\overline{\text{WE}}$ -and- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ (WCBR) refresh cycle. Refresh during test mode operation will be performed by normal read cycles or by WCBR refresh cycles. When the state of two test bits accord each other, the condition of the output data is high level. When the state of test bits do not accord, the condition of the output data is low level. In order to end this test mode operation, perform a $\overline{\text{RAS}}$ -only refresh cycle or a $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle.
 17. In a test mode read cycle, the value of t_{RAC} , t_{AA} , t_{CAC} , t_{OAC} and t_{ACP} is delayed for 2 ns to 5ns for the specified value. These parameters should be specified in test mode cycles by adding the above value to the specified value in this data sheet.
 18. Either t_{RCH} or t_{RRH} must be satisfied
 19. $t_{RAS}(\text{min}) = t_{RWD}(\text{min}) + t_{RWL}(\text{min}) + t_T$ in read-modify-write cycle.
 20. $t_{CAS}(\text{min}) = t_{CWD}(\text{min}) + t_{CWL}(\text{min}) + t_T$ in read-modify-write cycle.
 21. XXX: H or L (H: $V_{IH}(\text{min}) \leq V_{IN} \leq V_{IH}(\text{max})$, L: $V_{IL}(\text{min}) \leq V_{IN} \leq V_{IL}(\text{max})$)
 //////////////: Invalid Dout

Timing Waveforms*21

Read Cycle



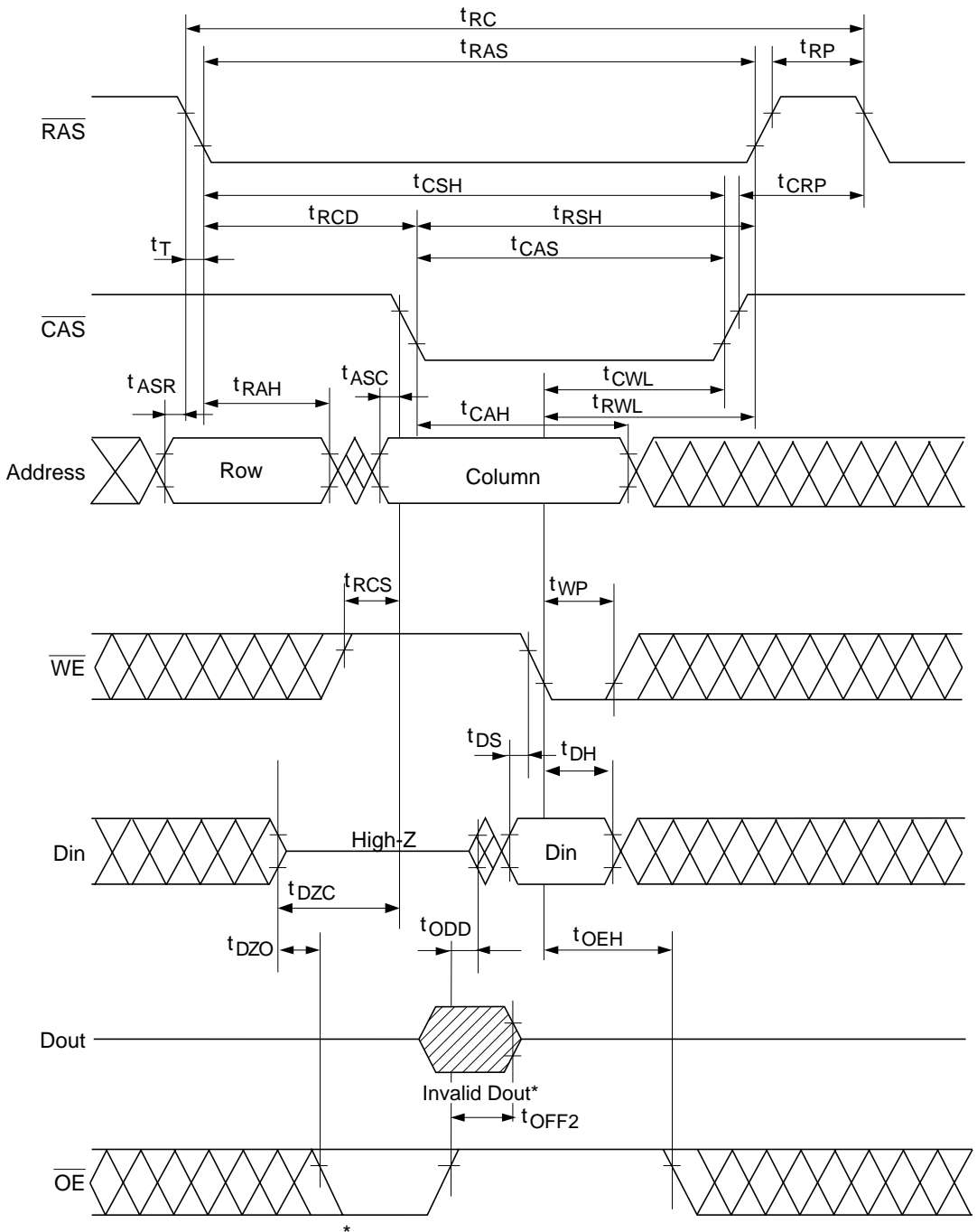
Early Write Cycle



* $t_{WCS} \geq t_{WCS}(\text{min})$

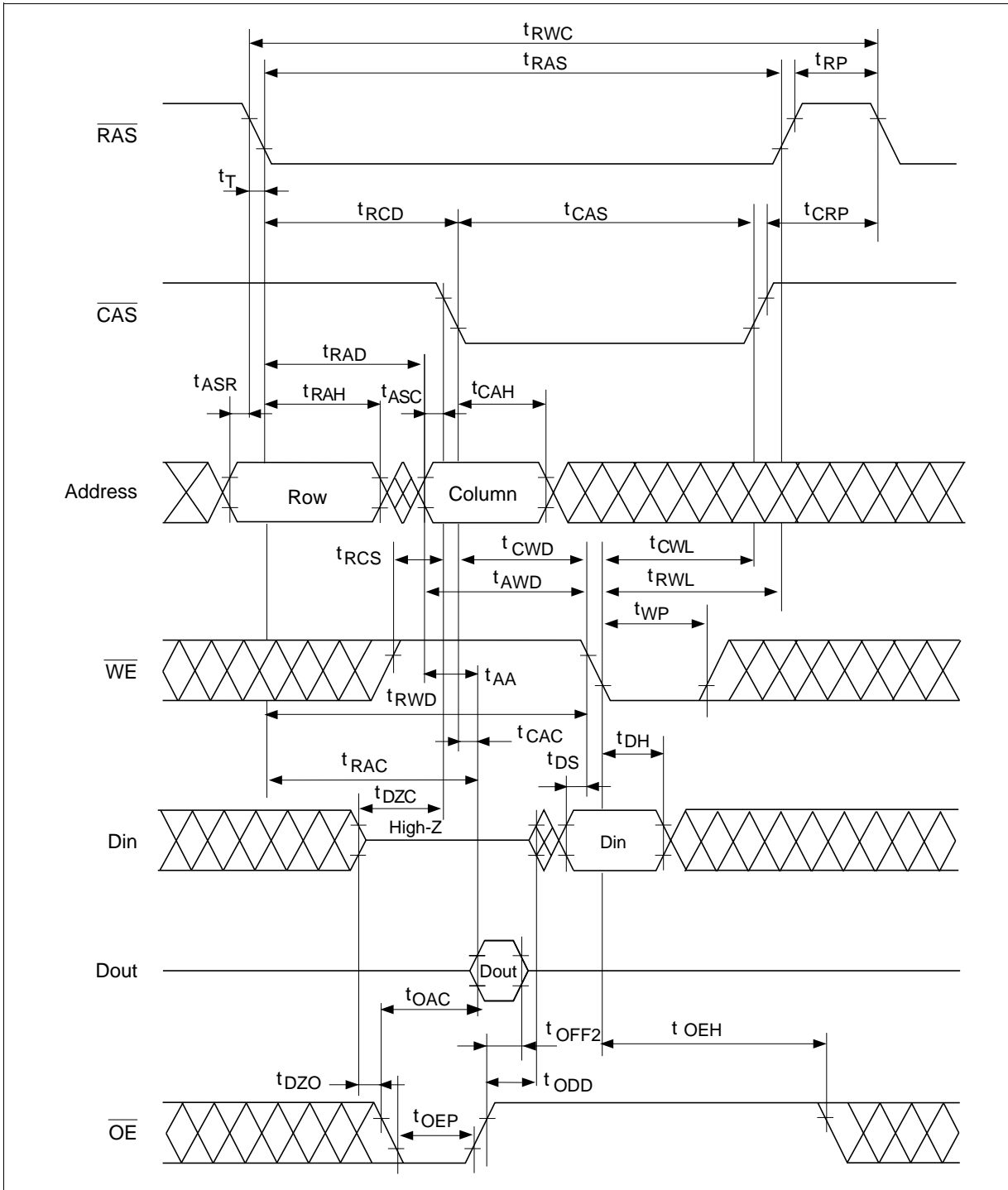
** OE : H or L

Delayed Write Cycle

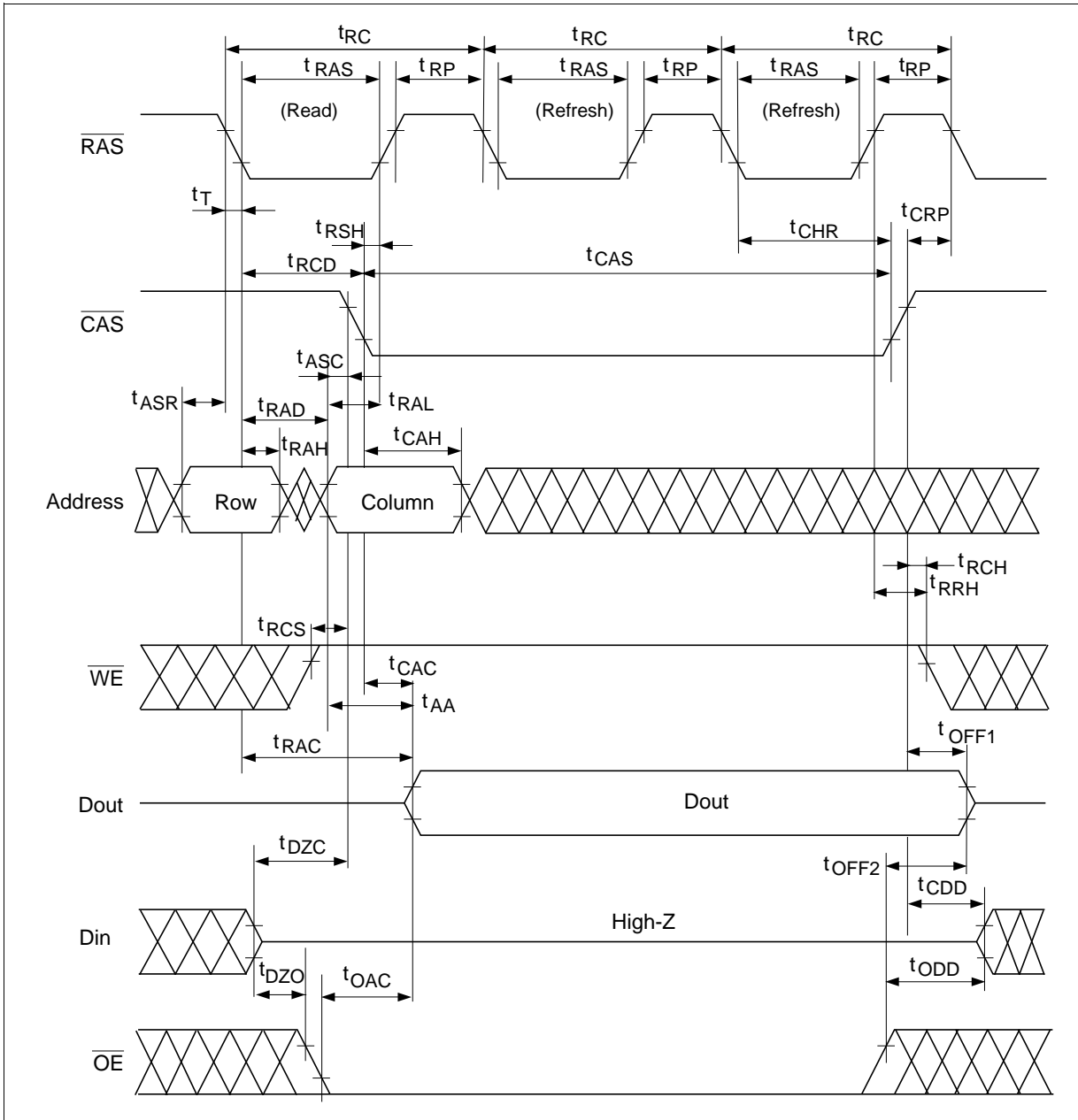


* Invalid Dout comes out, when \overline{OE} is low level.

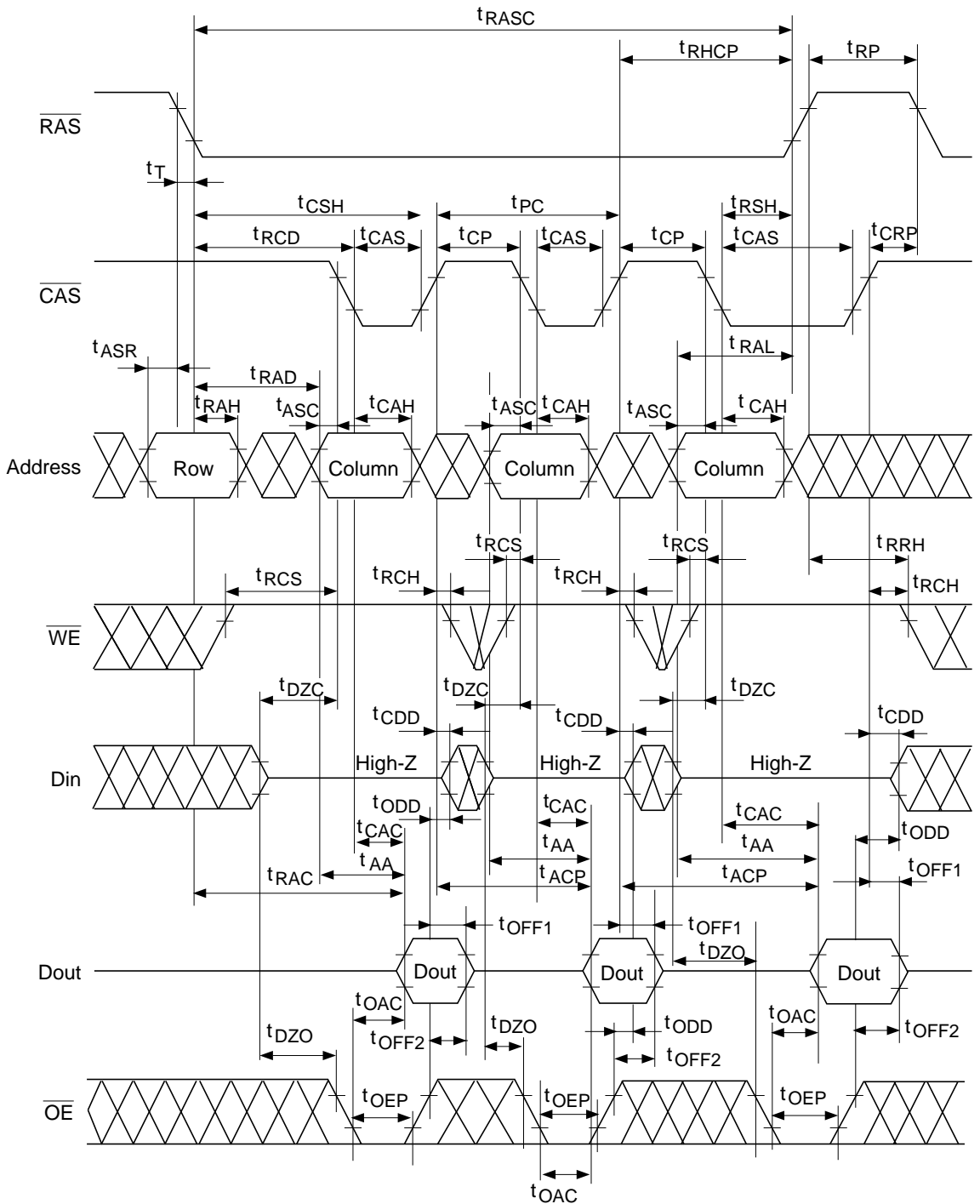
Read-Modify-Write Cycle



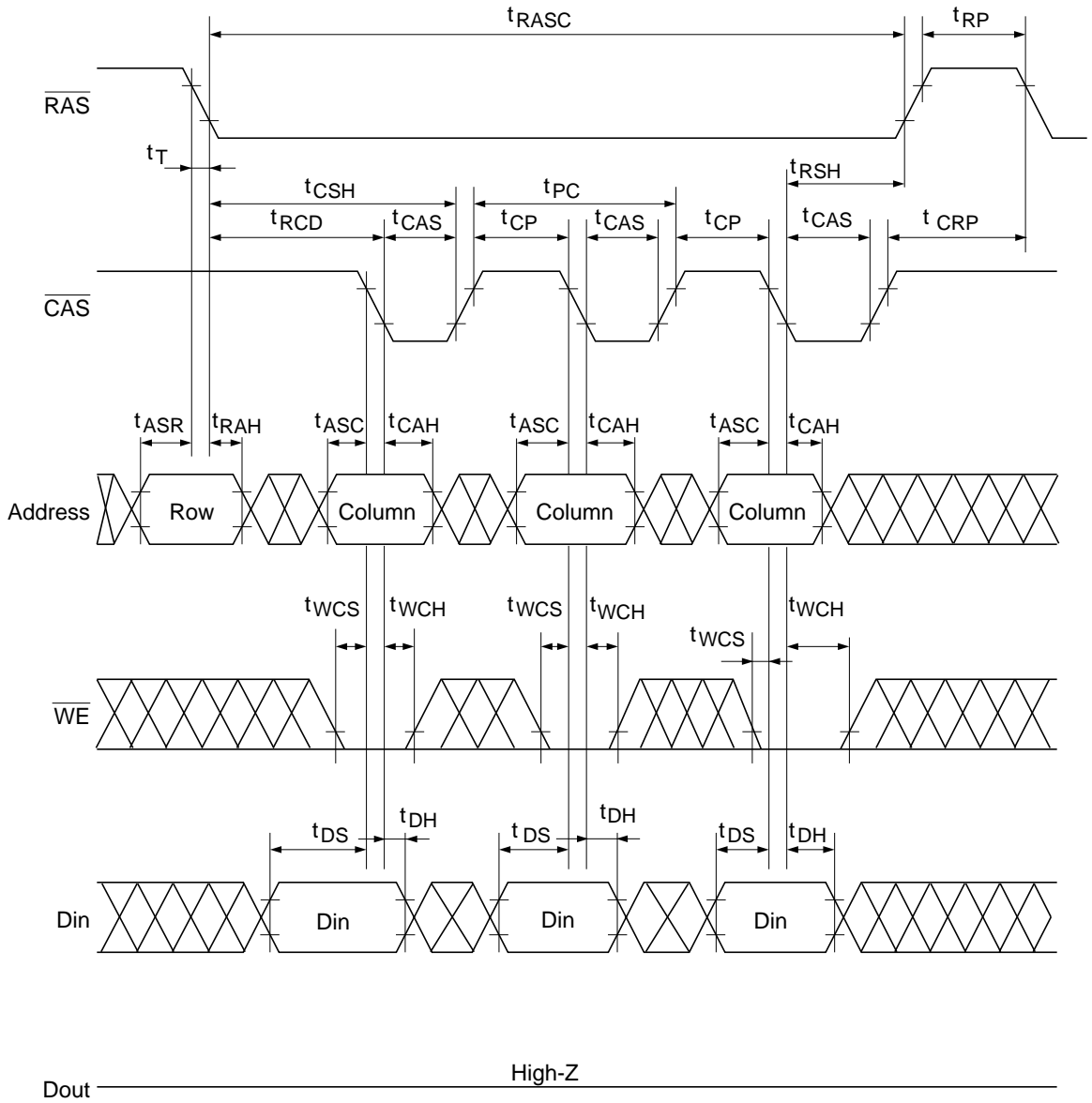
Hidden Refresh Cycle



Fast Page Mode Read Cycle

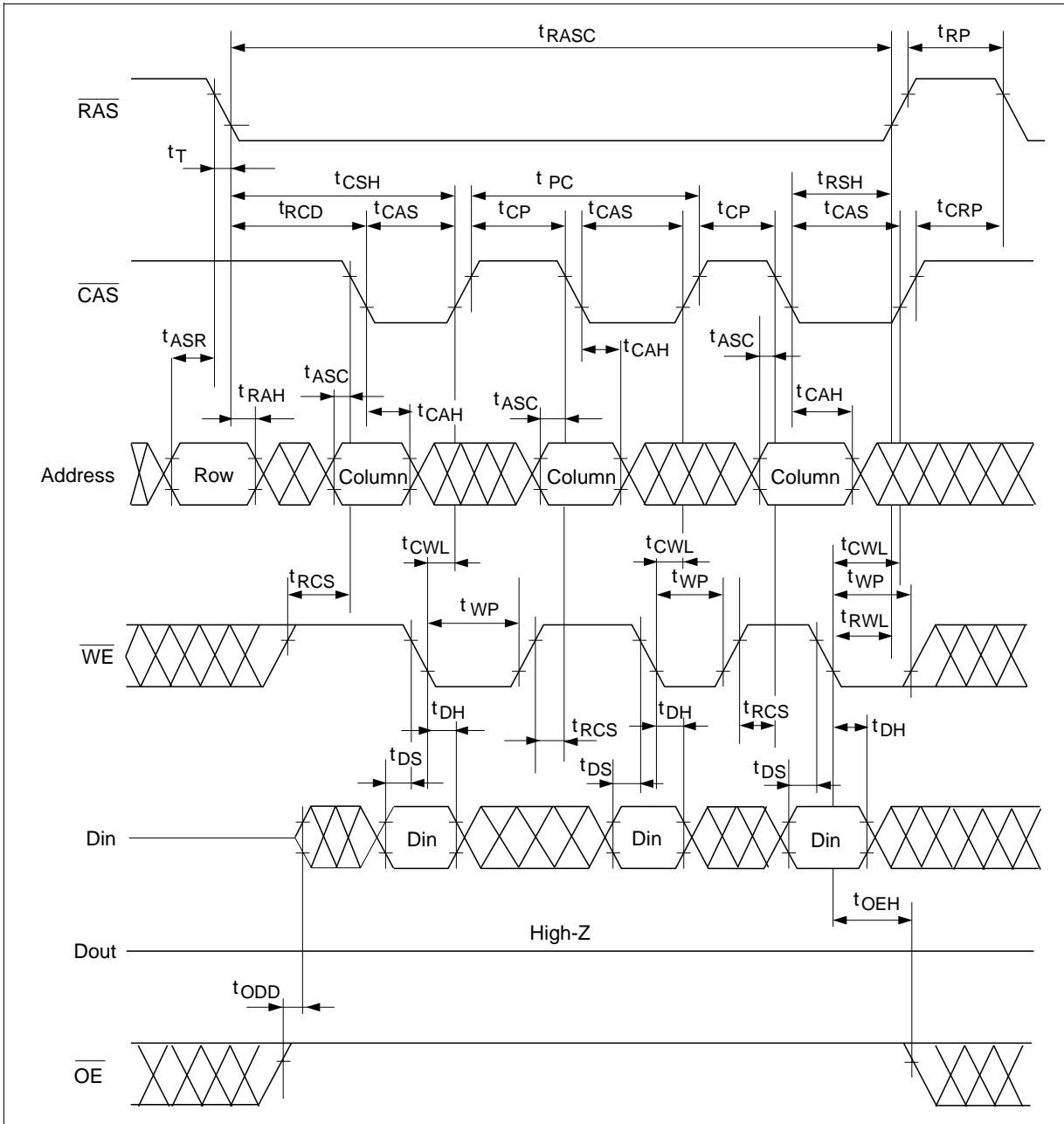


Fast Page Mode Early Write Cycle

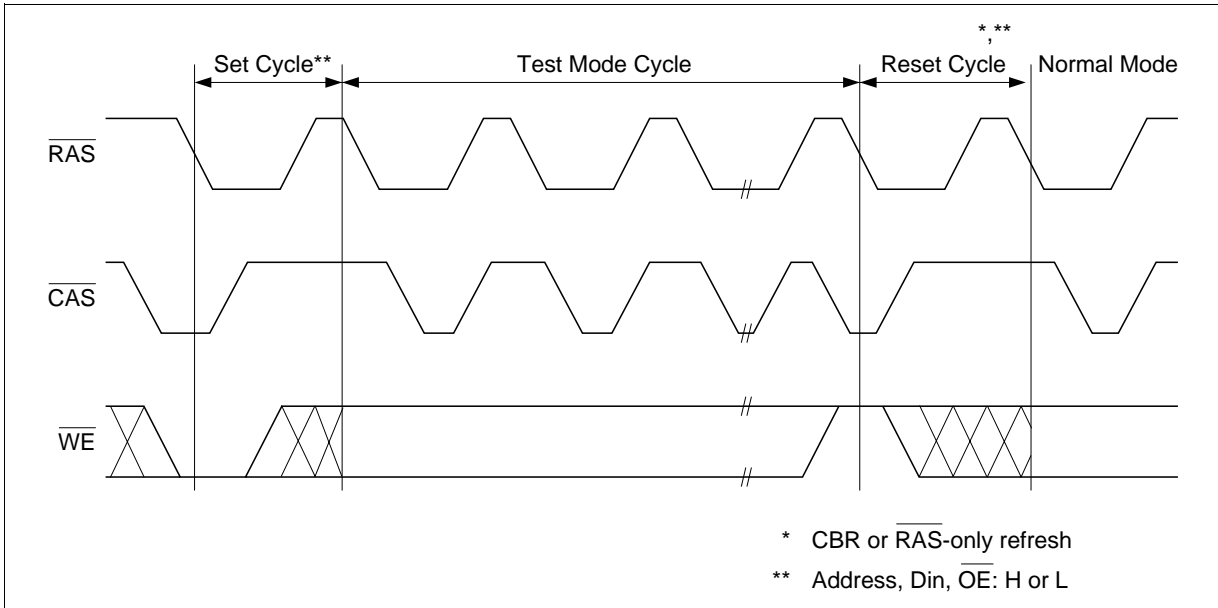


* \overline{OE} : H or L

Fast Page Mode Delayed Write Cycle

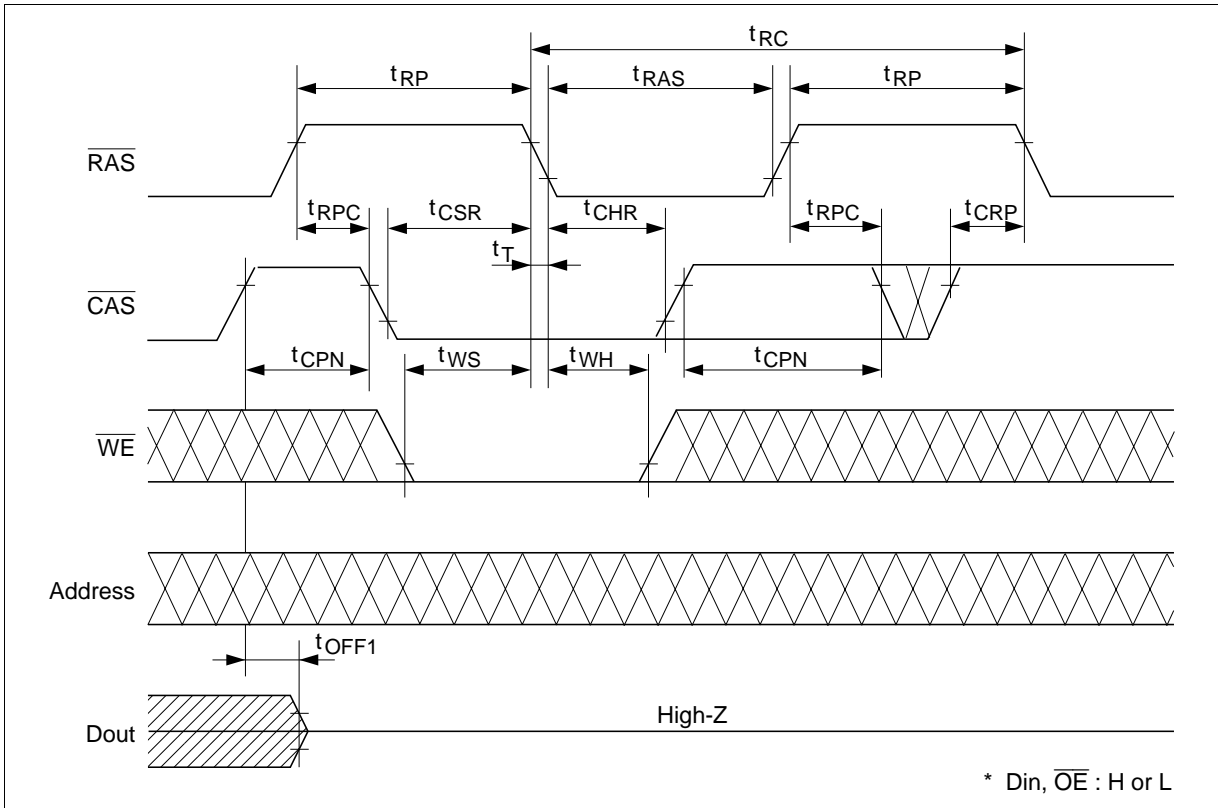


Test Mode Cycle

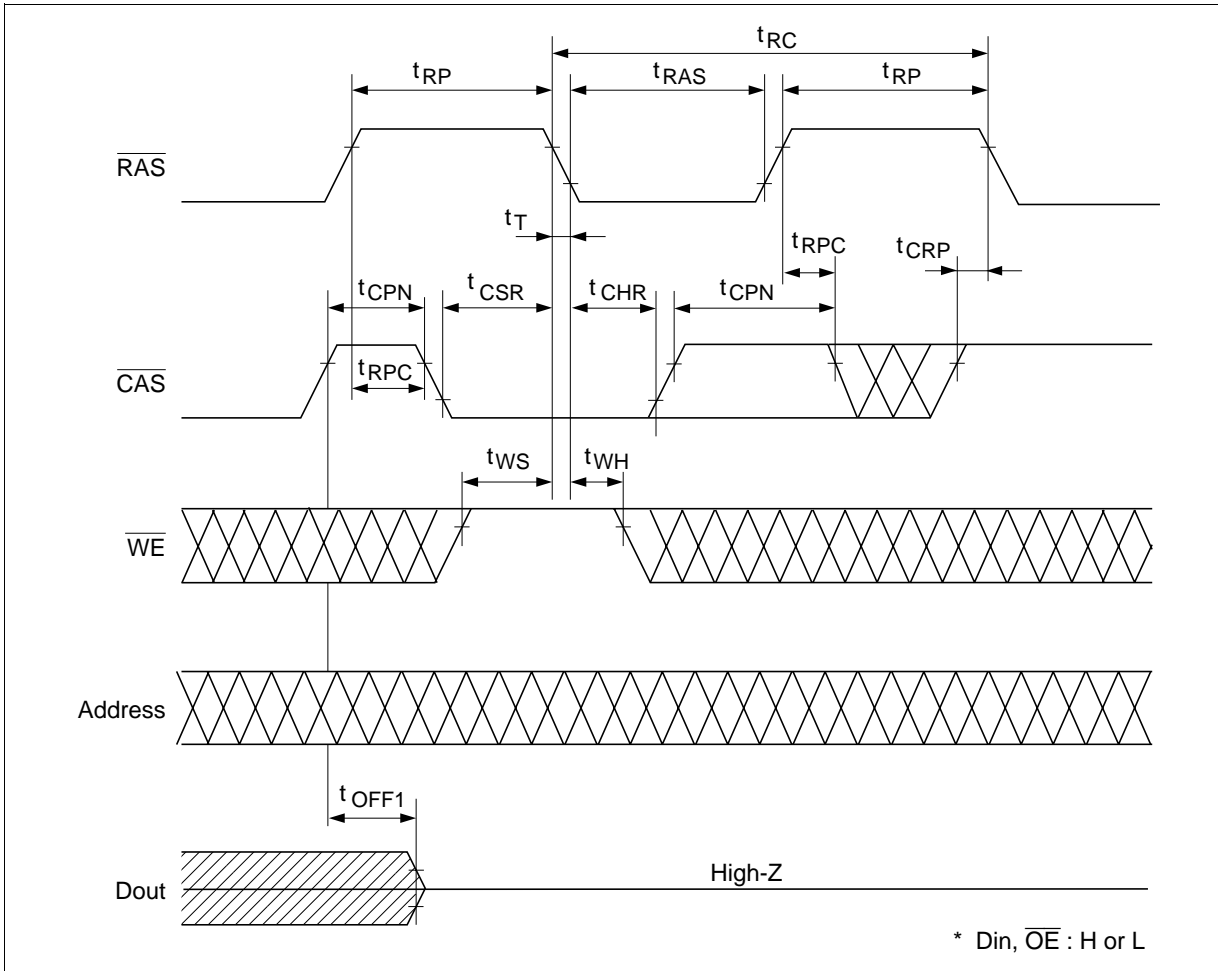


Test Mode Set Cycle

$\overline{\text{WE}}$ -and- $\overline{\text{CAS}}$ -Before $\overline{\text{RAS}}$ -Refresh Cycle

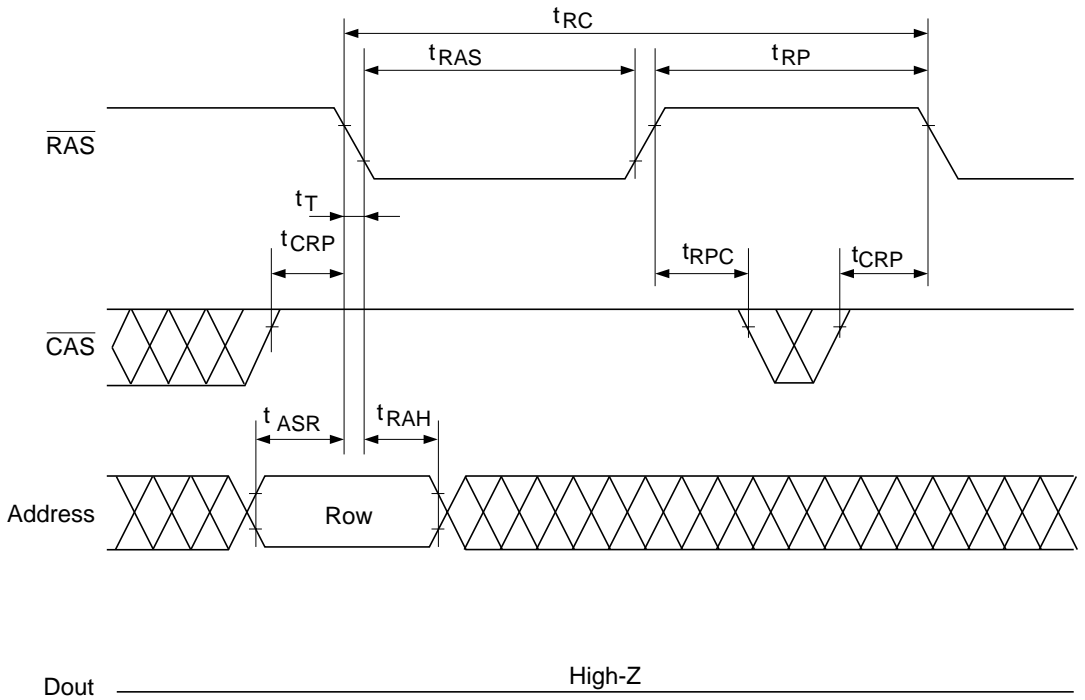


$\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh Cycle



HM514400C Series

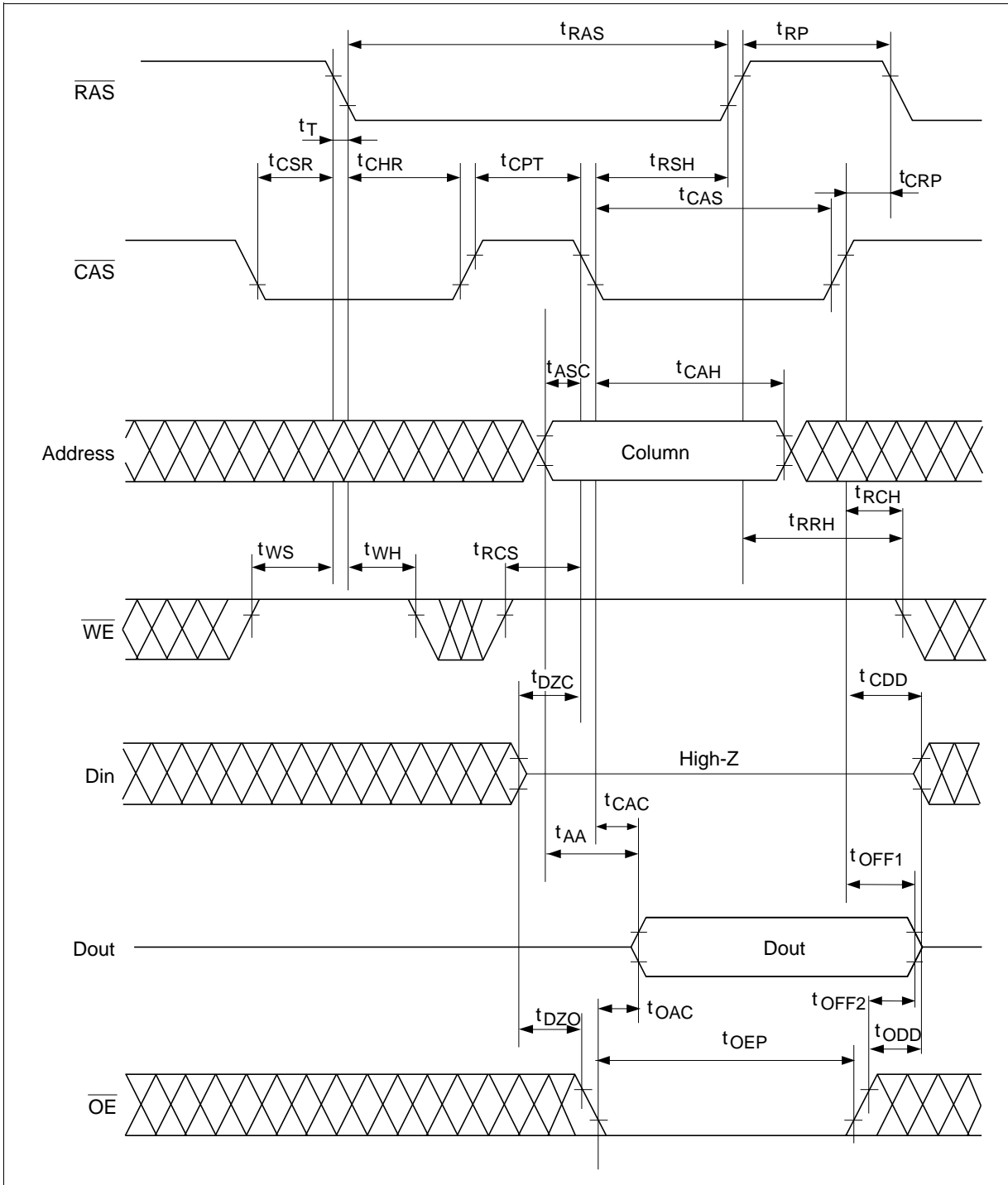
RAS-Only Refresh Cycle



* Refresh address : A0 – A9 (AX0 – AX9)

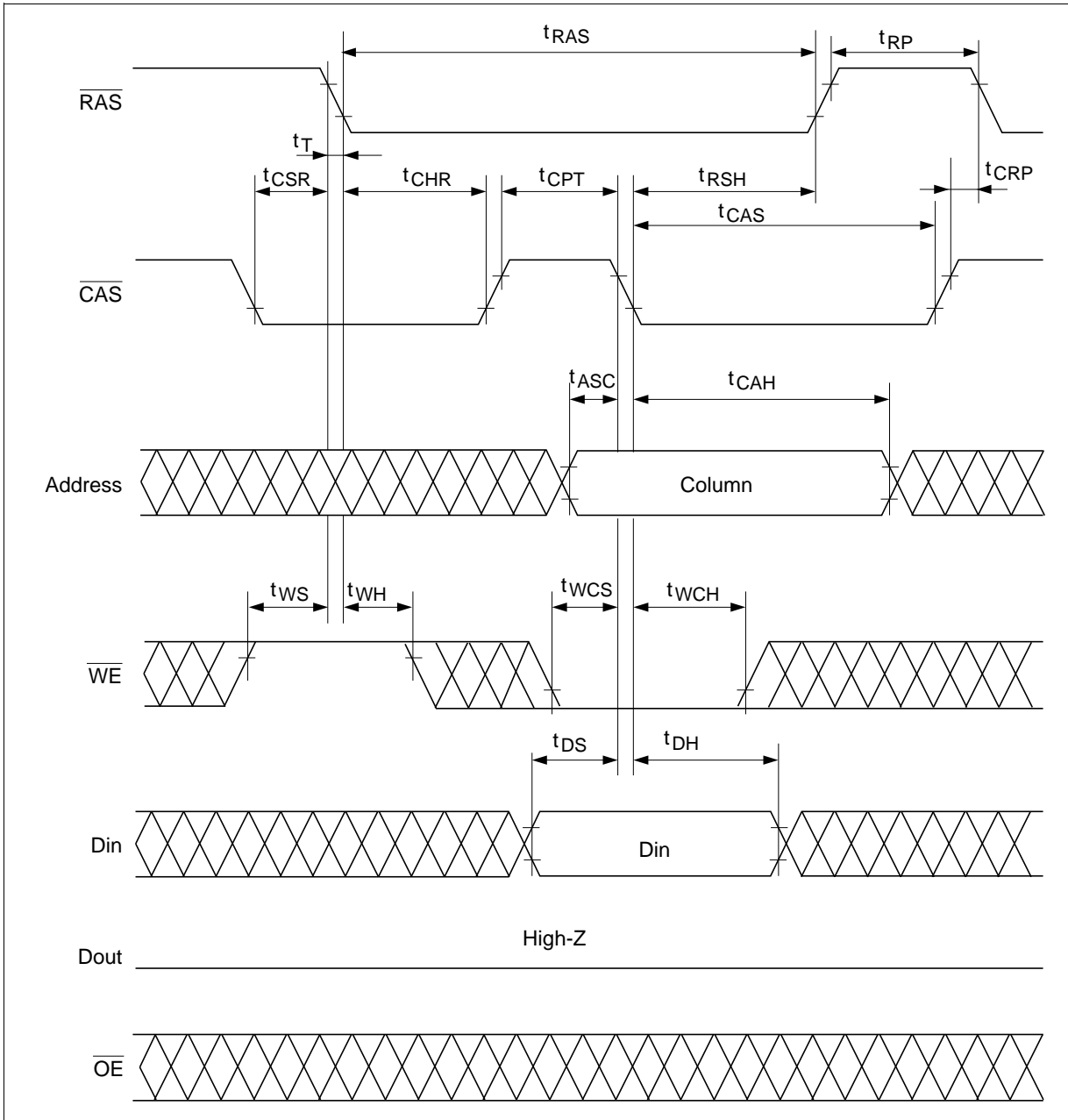
** Din, $\overline{\text{OE}}$, $\overline{\text{WE}}$: H or L

CAS-Before-RAS Refresh Counter Check Cycle (Read)



HM514400C Series

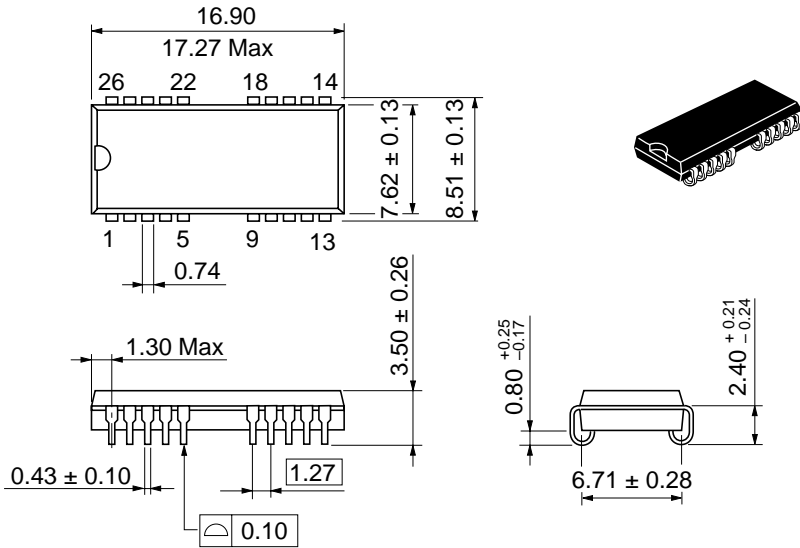
CAS-Before-RAS Refresh Counter Check Cycle (Write)



Package Dimensions

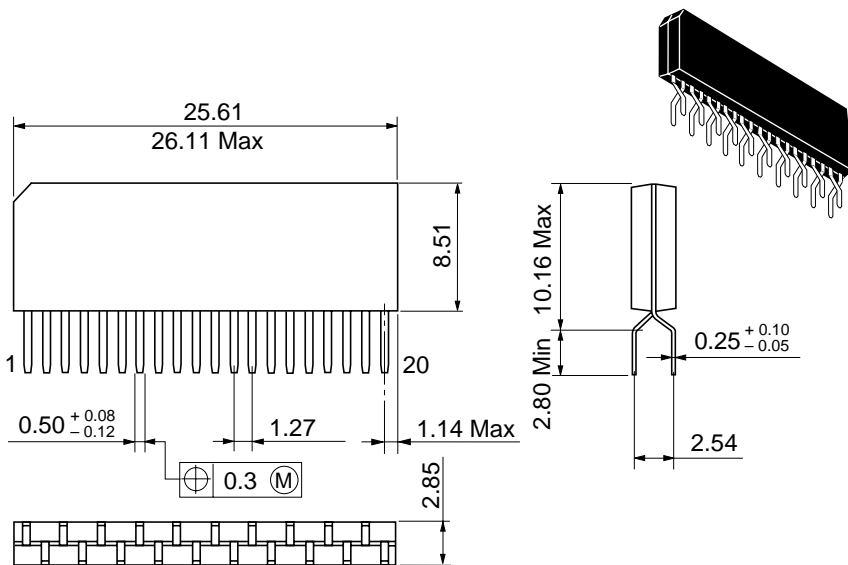
HM514400CS/CLS Series (CP-26/20D)

Unit: mm



HM514400CZ/CLZ Series (ZP-20)

Unit: mm



HM514400C Series

HM514400CTT/CLTT Series (TTP-26/20D)

Unit: mm

